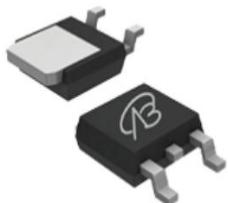


VBE1305 Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, c}	Q_g (Typ.)
30	0.0040at $V_{GS} = 10$ V	85	80 nC
	0.0050at $V_{GS} = 4.5$ V	70	

TO-252



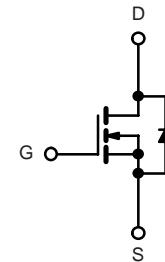
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested



APPLICATIONS

- Synchronous Rectification
- Power Supplies



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	30	V	
Gate-Source Voltage	V_{GS}	± 25		
Continuous Drain Current ($T_J = 175$ °C)	$T_C = 25$ °C	85 ^{a, c}	A	
	$T_C = 70$ °C	70 ^c		
	$T_A = 25$ °C	59 ^b		
	$T_A = 70$ °C	53 ^b		
Pulsed Drain Current	I_{DM}	255		
Avalanche Current Pulse	I_{AS}	80		
Single Pulse Avalanche Energy	E_{AS}	320	mJ	
Continuous Source-Drain Diode Current	$T_C = 25$ °C	110 ^{a, c}		
	$T_A = 25$ °C	2.6 ^b		
Maximum Power Dissipation	$T_C = 25$ °C	312 ^a	W	
	$T_C = 70$ °C	200		
	$T_A = 25$ °C	3.13 ^b		
	$T_A = 70$ °C	2.0 ^b		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	32	40	°C/W
Maximum Junction-to-Case	R_{thJC}	0.33	0.4	

Notes:

a. Based on $T_C = 25$ °C.

b. Surface Mounted on 1" x 1" FR4 board.

c. Calculated based on maximum junction temperature. Package limitation current is 110 A.

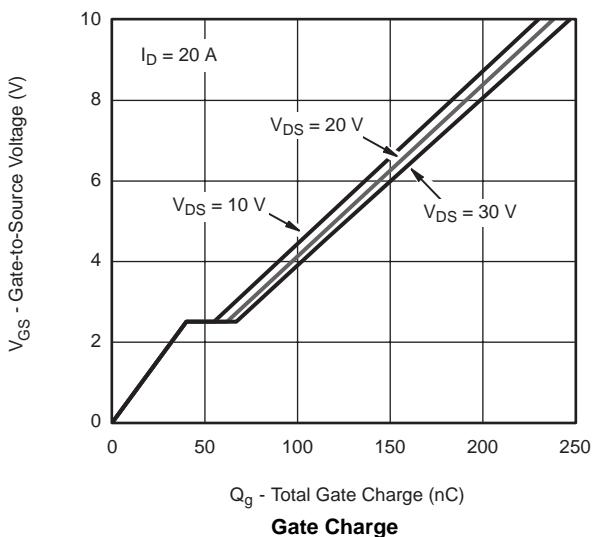
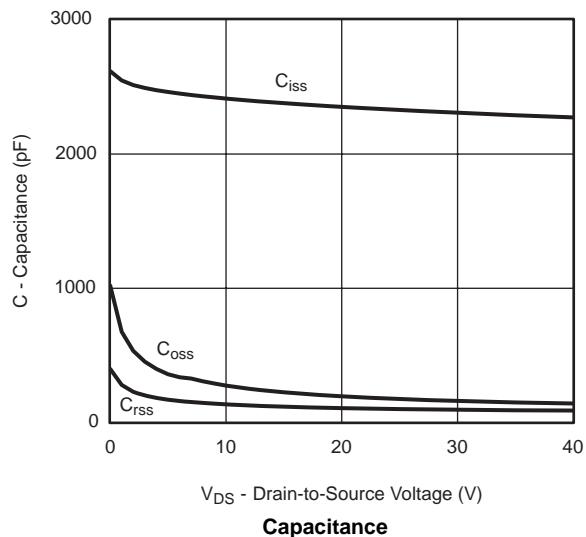
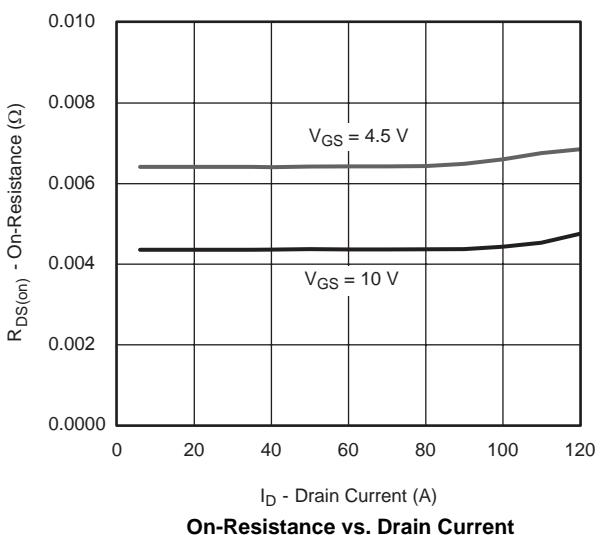
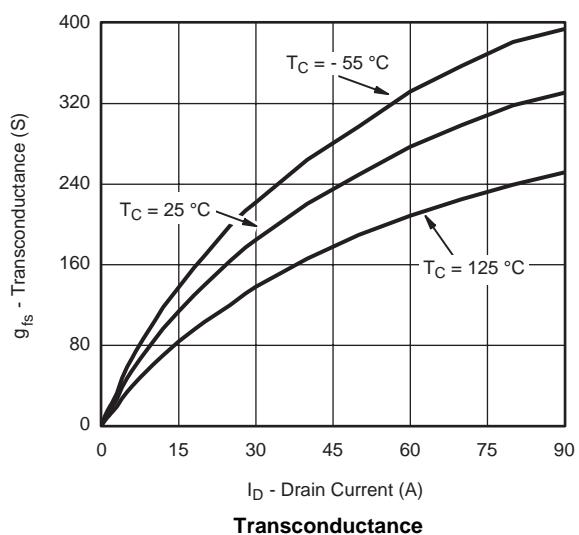
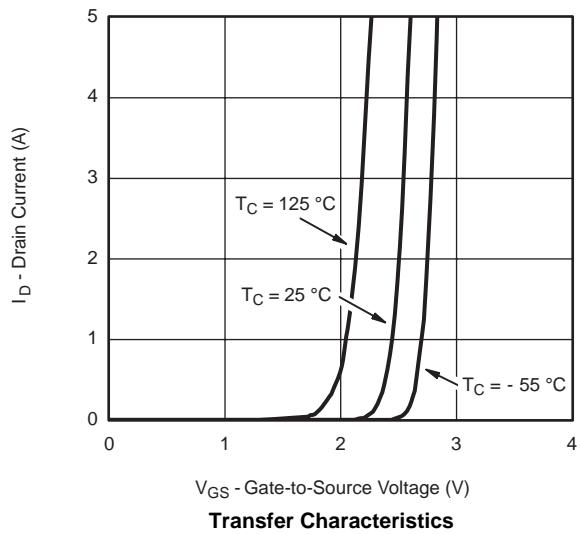
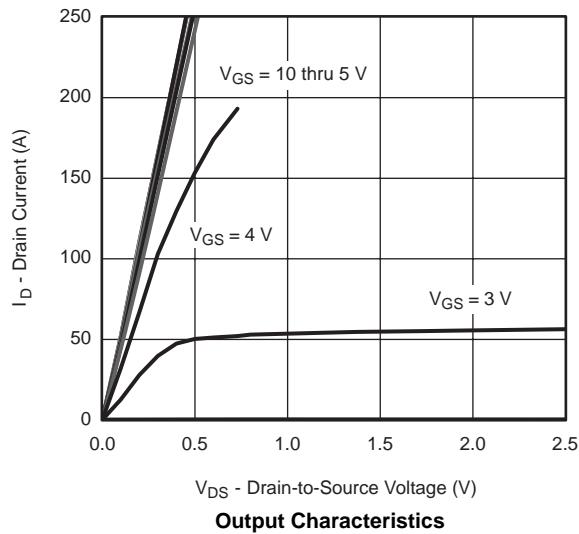
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

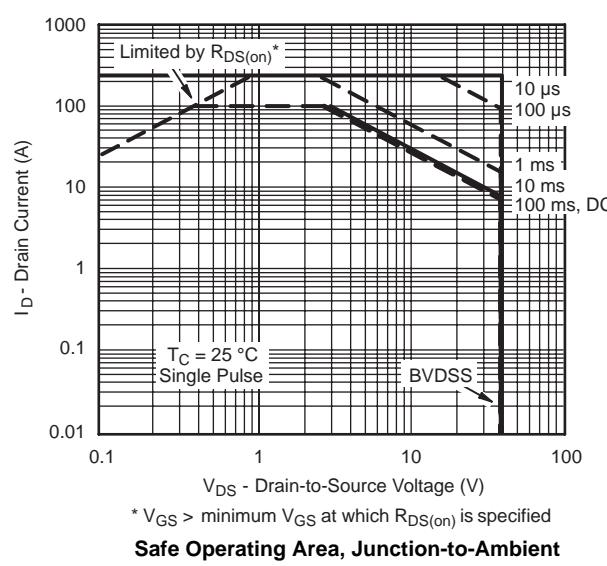
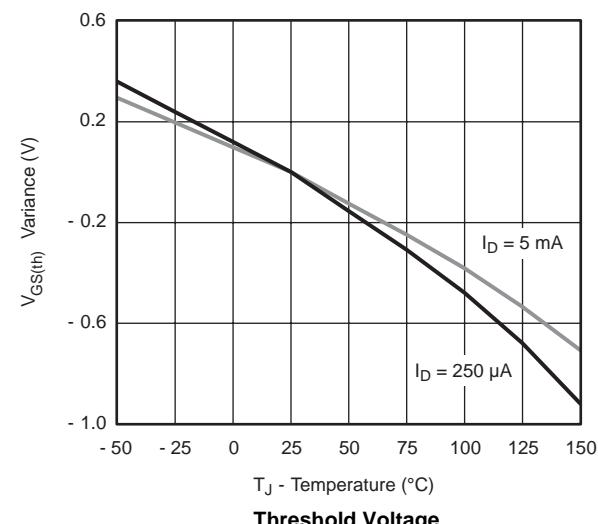
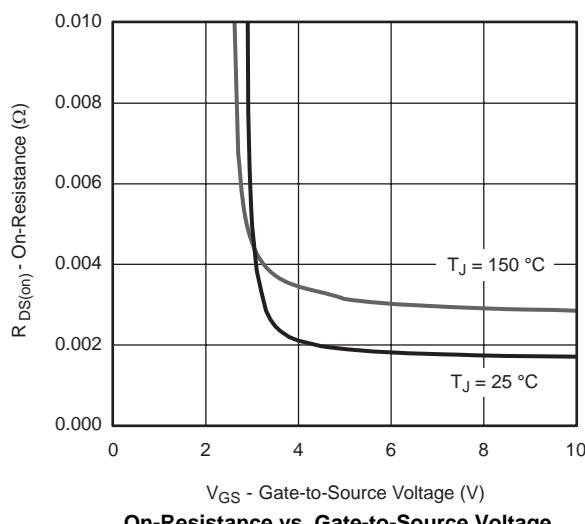
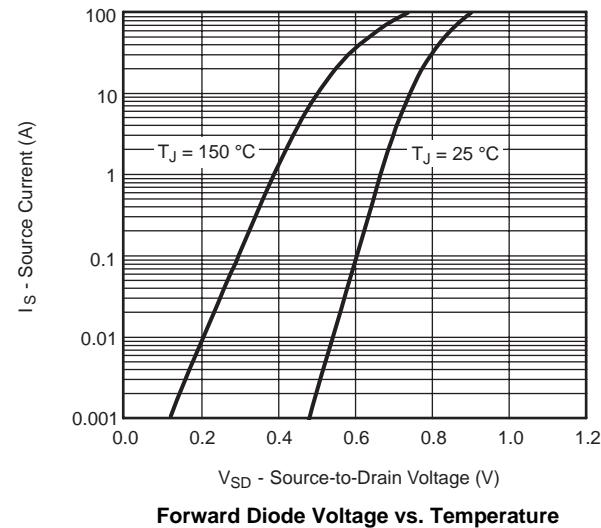
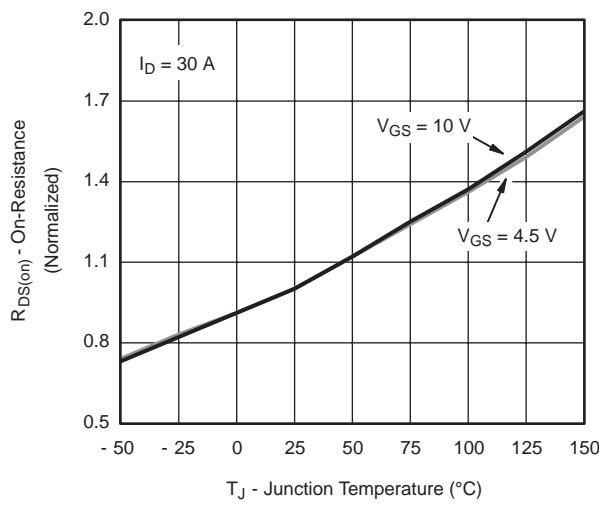
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \mu\text{A}$		41		$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ Temperature Coefficient	$\Delta V_{GS(\text{th})}/T_J$			-8		
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	1.2		2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} \geq 5 \text{ V}$, $V_{GS} = 10 \text{ V}$	120			A
Drain-Source On-State Resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$		0.0040		Ω
		$V_{GS} = 4.5 \text{ V}$, $I_D = 20 \text{ A}$		0.0050		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}$, $I_D = 30 \text{ A}$		180		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 20 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$		2400		pF
Output Capacitance	C_{oss}			550		
Reverse Transfer Capacitance	C_{rss}			250		
Total Gate Charge	Q_g	$V_{DS} = 20 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$		80	120	nC
Gate-Source Charge	Q_{gs}			20		
Gate-Drain Charge	Q_{gd}			12		
Gate Resistance	R_g		$f = 1 \text{ MHz}$		0.85	1.3
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = 20 \text{ V}$, $R_L = 1.0 \Omega$ $I_D \geq 20 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$		20	30	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(\text{off})}$			77	115	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(\text{on})}$			102	155	
Rise Time	t_r	$V_{DD} = 20 \text{ V}$, $R_L = 1.0 \Omega$ $I_D \geq 20 \text{ A}$, $V_{GEN} = 4.5 \text{ V}$, $R_g = 1 \Omega$		62	95	ns
Turn-Off Delay Time	$t_{d(\text{off})}$			180	270	
Fall Time	t_f			60	90	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25^\circ\text{C}$			85	A
Pulse Diode Forward Current ^a	I_{SM}				255	
Body Diode Voltage	V_{SD}	$I_S = 20 \text{ A}$		0.8	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		60	120	ns
Body Diode Reverse Recovery Charge	Q_{rr}			70	105	nC
Reverse Recovery Fall Time	t_a			30		ns
Reverse Recovery Rise Time	t_b			20		

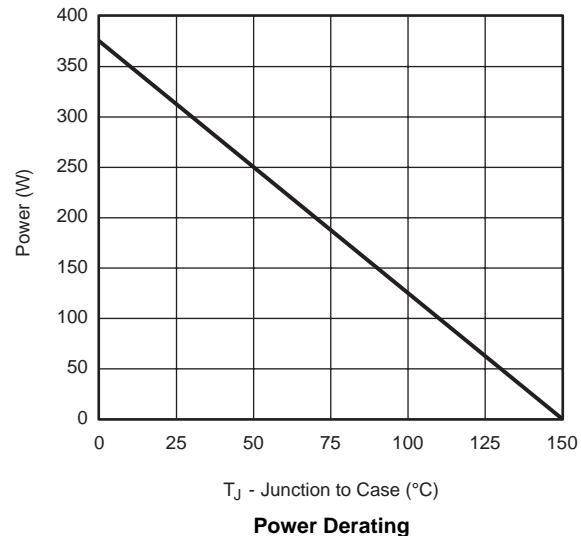
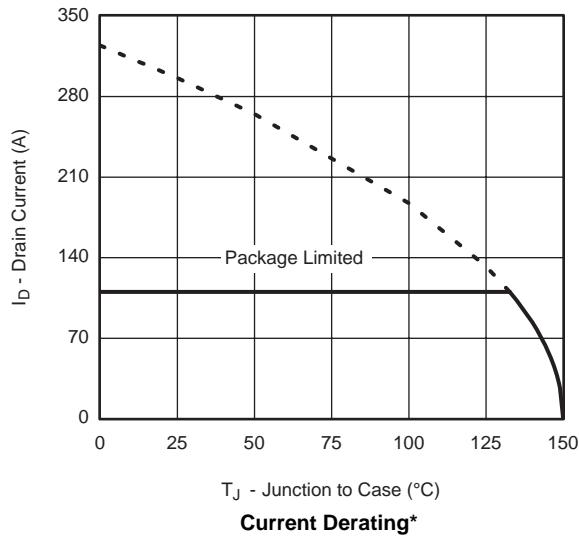
Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

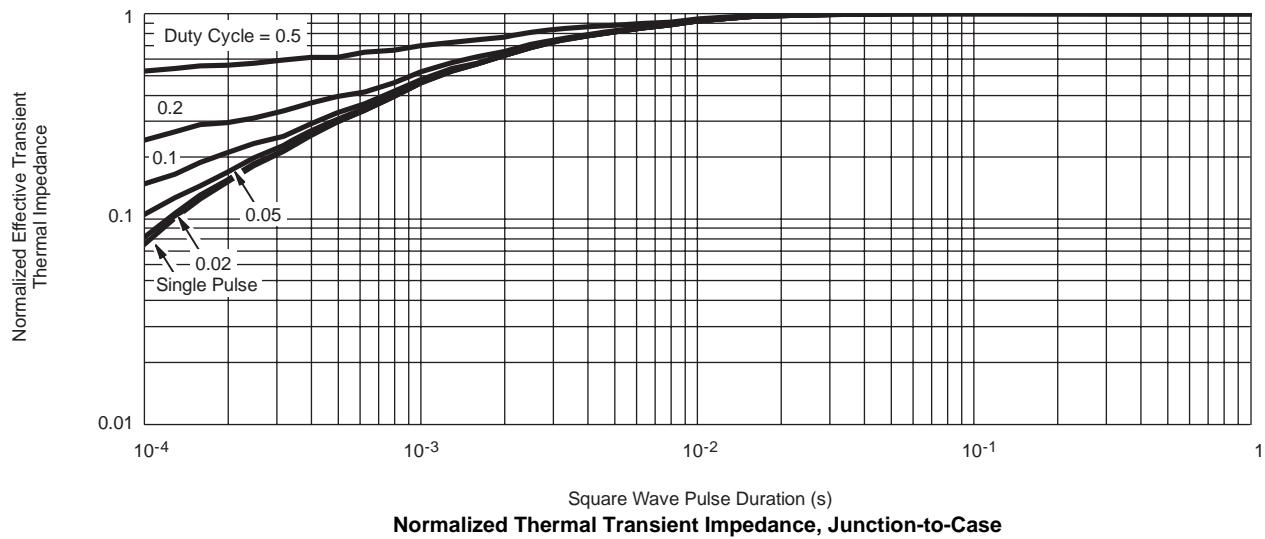
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


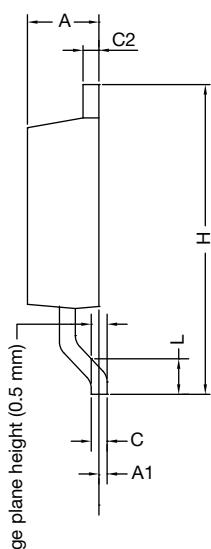
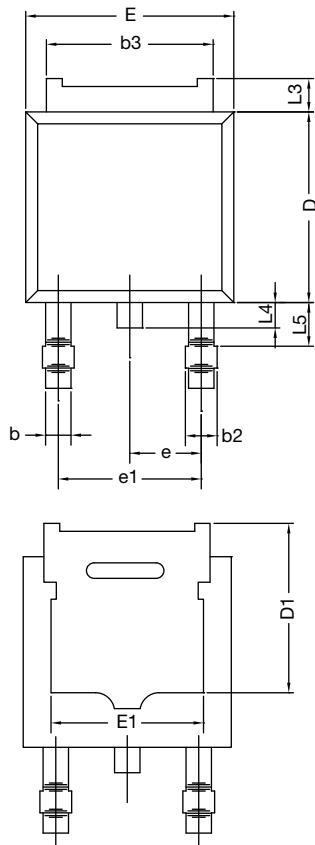
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TO-252AA CASE OUTLINE



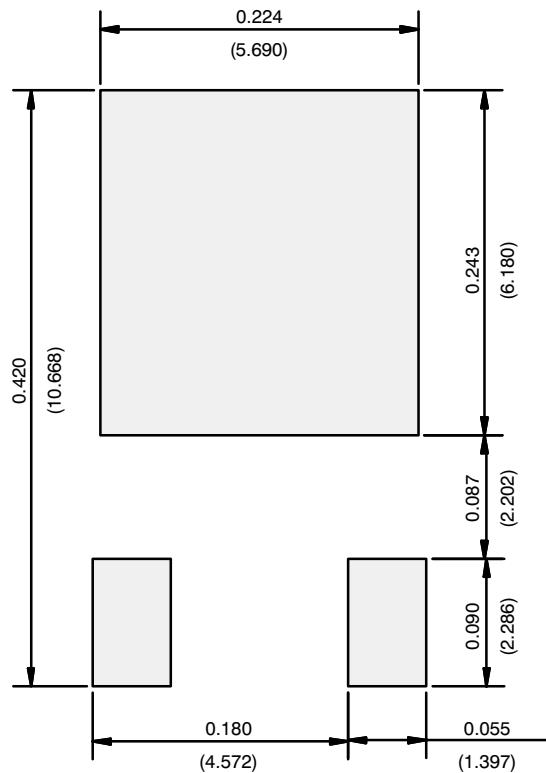
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060

ECN: X12-0247-Rev. M, 24-Dec-12
 DWG: 5347

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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